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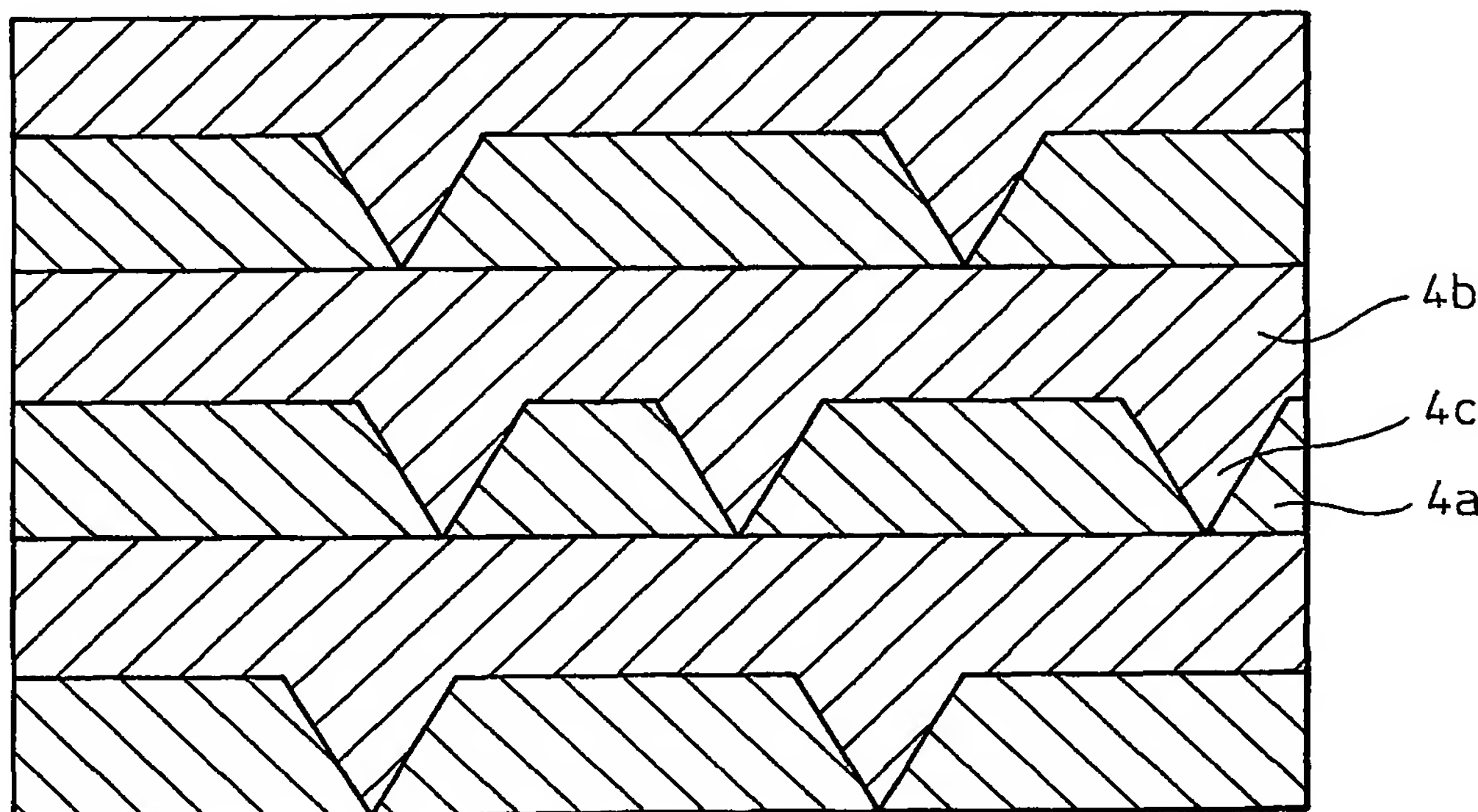
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[Continued on next page]

(54) Title: N-TYPE GROUP III NITRIDE SEMICONDUCTOR LAYERED STRUCTURE



(57) Abstract: An object of the present invention is to provide a low-resistance n-type Group III nitride semiconductor layered structure having excellent flatness and few pits. The inventive n-type group III nitride semiconductor layered structure comprises a substrate and, stacked on the substrate, an n-type impurity concentration periodic variation layer comprising an n-type impurity atom higher concentration layer and an n-type impurity atom lower concentration layer, said lower concentration layer being stacked on said higher concentration layer.

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